

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L15	2	bond adj pad and first adj mask and second adj mask and contiguous.clm.	US-PGPU B	OR	ON	2005/09/21 15:45
L16	1	(bond adj pad and first adj mask and second adj mask and contiguous).clm.	US-PGPU B	OR	ON	2005/09/21 15:45

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	8707	(bond\$3 adj pad) with (trench via hole damascene groove aperture)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:14
L2	11037	(bond\$3 adj pad) with (trench via hole groove aperture damascene aperture opening recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:07
L3	4687	2 and (dielectric insulat\$3) with (trench via hole groove aperture damascene aperture opening recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:07
L4	1966	3 and (mask masking resist photoresist) with (trench via hole groove aperture damascene aperture opening recess)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:08
L5	1966	4 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:09
L6	1755	5 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator) with etch\$4	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:10
L7	951	6 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator) with ('cu' copper)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:11

L8	608	7 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator) with (two)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:11
L9	126	7 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator) with (two different difference) near5 (part area region)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:12
L10	122	8 and (mask masking resist photoresist trench via hole groove aperture damascene aperture opening recess bond bonding pad dielectric insulating insulator) with (two different difference) near5 (part area region)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:12
L11	376	8 and (bond\$3 adj pad) with (method process)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:14
L12	250	8 and (bond\$3 adj pad) near5 (method process)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 12:37
L13	1	10/701423	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 12:38
L14	1	10/837528	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 12:38
S1	1	10/654240	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/13 17:33

S3	3	"6362090"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/13 18:42
S4	17839	((dielectric insulat\$3) with (trench via hole damascene groove aperture)) with mask\$3	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:05
S5	9987	S4 and (dielectric insulat\$3) with (photoresist resist)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/13 18:45
S6	201	S5 and (dielectric insulat\$3) with (bond\$3 adj pad)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/21 10:05
S7	107	S6 and ('cu' copper interconnect\$3) with (bond\$3 adj pad)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 06:51
S8	3	"6452271"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 06:52
S9	4	"6445069"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 06:55
S10	6	"6444489"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:00
S11	1	"6424090"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:01
S12	17	"6153940"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:04
S13	17	"6153940"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:05

S14	39	"3986255"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:05
S15	16458	((bonding bond) near3 pad) with (substrate dielectric insulat\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:09
S16	6774	S15 and ((bonding bond) near3 pad) with (trench hole via groove aperture opening)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:10
S17	343	S16 and ((mask\$3 photoresist resist) near3 pad) with (trench hole via groove aperture opening)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 07:11
S18	124	S17 and ('cu' copper) with (trench hole via groove aperture opening)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 08:34
S19	1	10/964019	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/09/14 08:34